

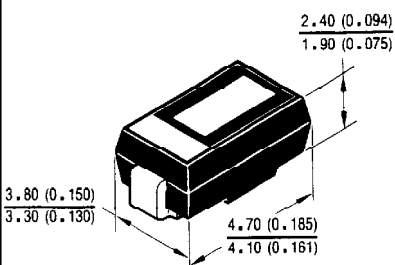
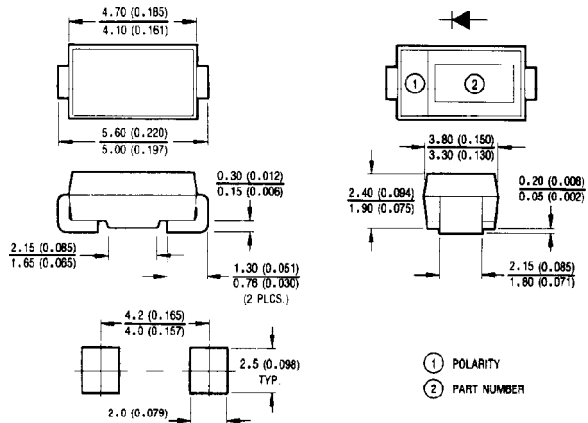
Major Ratings and Characteristics

Characteristics	10BQ100	Units
$I_{F(AV)}$ Rectangular waveform	1.0	A
V_{RRM}	100	V
I_{FSM} @ $t_p = 5\mu s$ sine	780	A
V_F @ 1.0Apk, $T_J = 125^\circ C$	0.62	V
T_J	-55 to 175	$^\circ C$

Description / Features

The 10BQ100 surface-mount Schottky rectifier has been designed for applications requiring very low forward drop and small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, free-wheeling diodes, battery charging and reverse battery protection.

- Small footprint, surface mountable
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long-term reliability

SMB	
CASE STYLE	CASE OUTLINE
	 <p>① POLARITY ② PART NUMBER</p>

10BQ100



Voltage Ratings

Part number	10BQ100
V _R Max. DC Reverse Voltage (V)	100
V _{RWM} Max. Working Peak Reverse Voltage (V)	

Absolute Maximum Ratings

Parameters		10BQ	Units	Conditions	
I _{F(AV)}	Max. Average Forward Current See Fig. 5	1.0	A	50% duty cycle @ T _C = 152°C, rectangular waveform	
I _{FSM}	Max. Peak One Cycle Non - Repetitive Surge Current — see Fig. 7	780	A	5μs Sine or 3μs Rect. pulse	Following any rated load condition and with rated V _{RRM} applied.
		38		10ms Sine or 6ms Rect. pulse	
E _{AS}	Non - Repetitive Avalanche Energy	9.7	mJ	T _J = 25°C, I _{AS} = 1.0A, L = 11mH	
I _{AR}	Repetitive Avalanche Current	1.0	A	Current decaying linearly to zero in 1μsec Frequency limited by T _J max. V _A = 1.5 X V _R typical	

Electrical Specifications

Parameters		10BQ	Units		Conditions
V _{FM}	Max. Forward Voltage Drop See Fig. 1 ①	0.78	V	@ 1.0A	T _J = 25°C
		0.87	V	@ 2.0A	
		0.62	V	@ 1.0A	T _J = 125°C
		0.70	V	@ 2.0A	
I _{RM}	Max. Reverse Leakage Current ① See Fig. 2	0.5	mA	T _J = 25°C	V _R = rated V _R
		1.0	mA	T _J = 125°C	
C _T	Max. Junction Capacitance	42	pF	V _R = 5V _{DC} , (test signal range 100KHz to 1MHz) 25°C	
L _S	Typical Series Inductance	2.0	nH	Measured lead to lead 5mm from package body	
dv/dt	Max. Voltage Rate of Change (Rated V _R)	10,000	V/μs		

Thermal-Mechanical Specifications

Parameters	10BQ	Units	Conditions
T _J Max. Junction Temperature Range	-55 to 175	°C	
T _{STG} Max. Storage Temperature Range	-55 to 175	°C	
R _{thJA} Max. Thermal Resistance, Junction to Ambient	140	°C/W	DC operation — See Fig. 4
R _{thJL} Max. Thermal Resistance, Junction to Lead ②	36	°C/W	DC operation
wt Approximate Weight	0.10	g	
Case Style	SMB		Similar to DO-214AA

① Pulse Width < 300μs, Duty Cycle < 2%

② Mounted 1 inch square PCB, thermal probe connected to lead 2mm from package

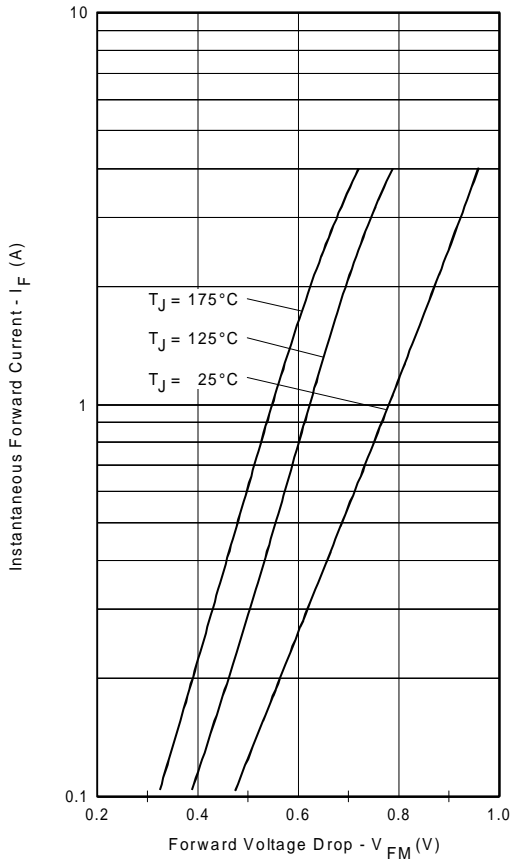


Fig. 1 Max. Forward Voltage Drop Characteristics

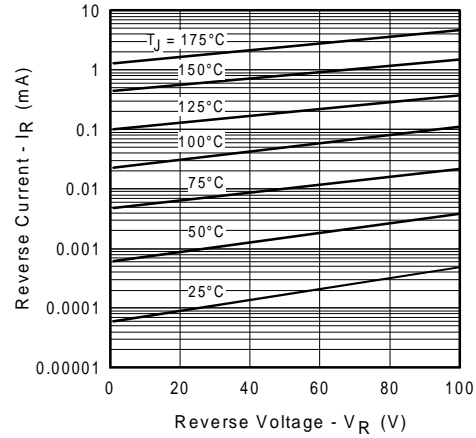


Fig. 2 Typical Values of Reverse Current Vs. Reverse Voltage

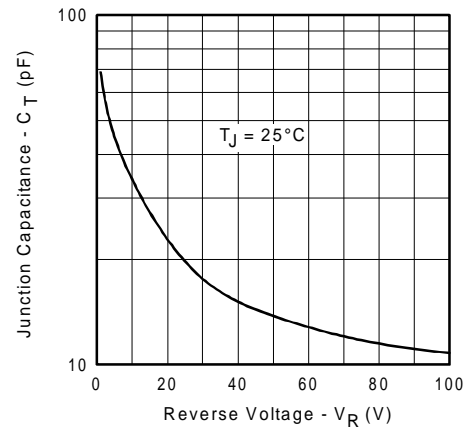


Fig. 3 Typical Junction Capacitance Vs. Reverse Voltage

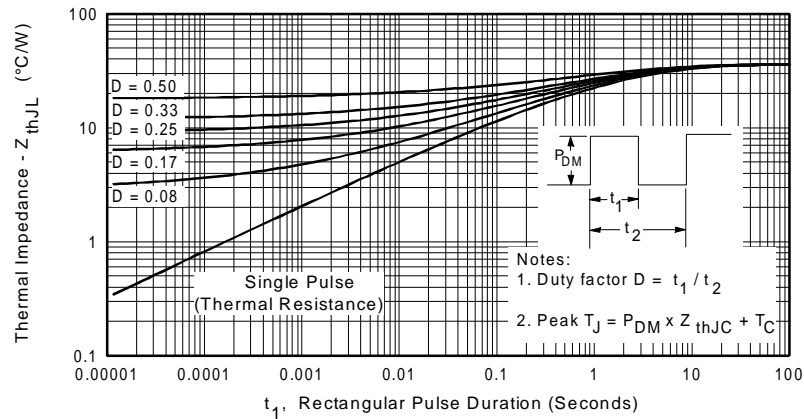


Fig. 4 Max. Thermal Impedance Z_{thJL} Characteristics

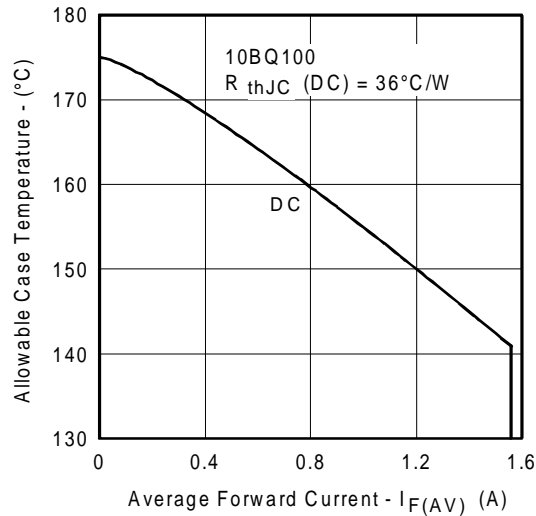


Fig. 5 Max. Allowable Case Temperature Vs. Average Forward Current

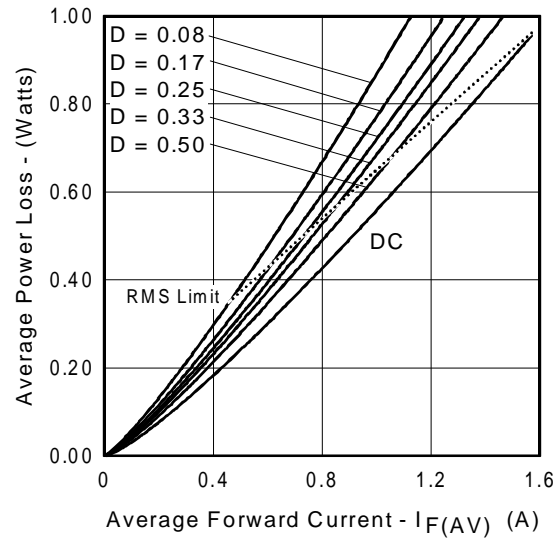


Fig. 6 Forward Power Loss Characteristics

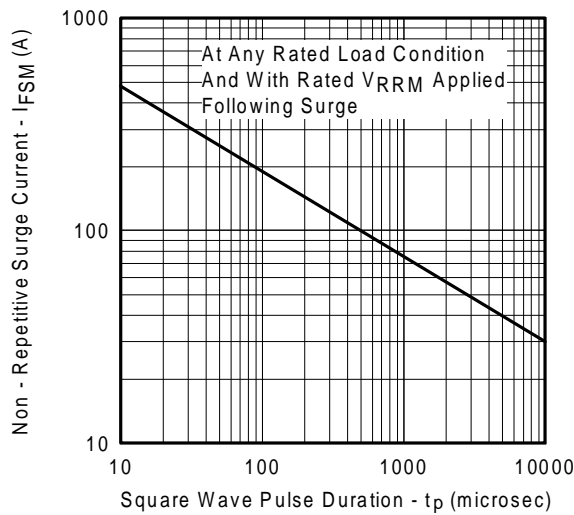


Fig. 7 Max. Non-Repetitive Surge Current

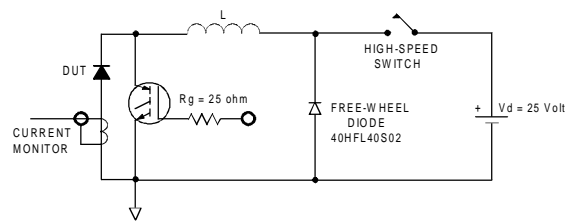


Fig. 8 Unclamped Inductive Test Circuit

Refer to the Appendix Section for the following:

Appendix D: Tape and Reel Information — See page 338.